August 2015

FDN5630

60V N-Channel PowerTrench® MOSFET

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

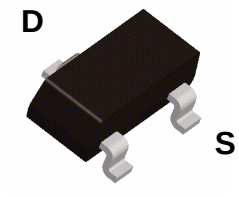
This MOSFET features very low $R_{DS(ON)}$ in a small SOT23 footprint. Fairchild's PowerTrench technology provides faster switching than other MOSFETs with comparable $R_{DS(ON)}$ specifications. The result is higher overall efficiency with less board space.

Features

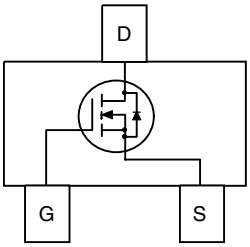
- 1.7 A, 60 V. $R_{DS(ON)}$ = 0.100 Ω @ V_{GS} = 10 V
  $R_{DS(ON)}$ = 0.120 Ω @ V_{GS} = 6 V.
- Optimized for use in high frequency DC/DC converters.
- Low gate charge.
- Very fast switching.
- SuperSOT™ - 3 provides low $R_{DS(ON)}$ in SOT23 footprint.

Applications

- DC/DC converter
- Motor drives



SuperSOT™-3



Absolute Maximum Ratings T_A = 25 C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Drain Current - Continuous	(Note 1a)	1.7	A
	- Pulsed		10	
P_D	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T_J, T_{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
5630	FDN5630	7	8mm	3000 units

Electrical Characteristics

T_A = 25 C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 µA,Referenced to 25°C		63		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 48 V, V_{GS} = 0 V			1	µA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -20 V, V_{DS} = 0 V			-100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	1	2.4	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 µA,Referenced to 25°C		6.9		mV/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 1.7 A V_{GS} = 10 V, I_D = 1.7 A, T_J = 125°C V_{GS} = 6 V, I_D = 1.6 A		0.073 0.127 0.083	0.100 0.180 0.120	Ω
$I_{D(on)}$	On-State Drain Current	V_{GS} = 10 V, V_{DS} = 1.7 V	5			A
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 1.7 A		6		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz		400	560	pF
C_{oss}	Output Capacitance			65	95	pF
C_{rss}	Reverse Transfer Capacitance			27	40	pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 30 V, I_D = 1 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		10	20	ns
t_r	Turn-On Rise Time			6	15	ns
$t_{d(off)}$	Turn-Off Delay Time			15	28	ns
t_f	Turn-Off Fall Time			5	15	ns
Q_g	Total Gate Charge	V_{DS} = 20 V, I_D = 1.7 A, V_{GS} = 10 V,		7	10	nC
Q_{gs}	Gate-Source Charge			1.6		nC
Q_{gd}	Gate-Drain Charge			1.2		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current				0.42	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 0.42 A (Note 2)		0.72	1.2	V

Notes:

1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

a) 250°C/W when mounted on a 0.02 in^2 Pad of 2 oz. Cu.

b) 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2: Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%

Typical Characteristics

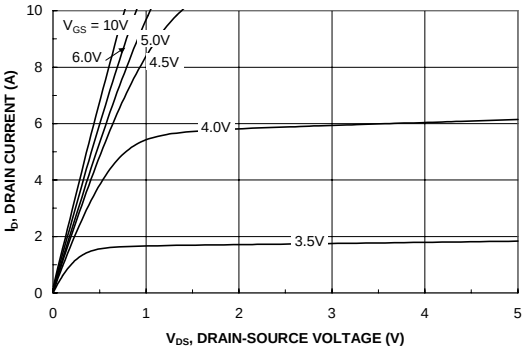


Figure 1. On-Region Characteristics.

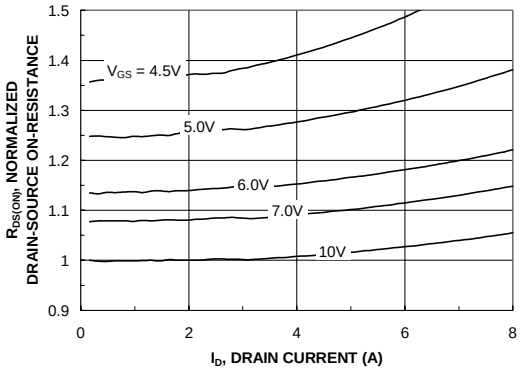


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

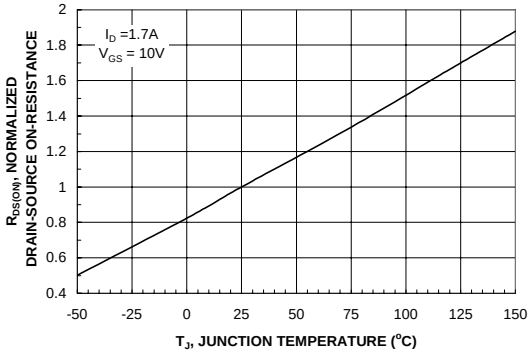


Figure 3. On-Resistance Variation with Temperature.

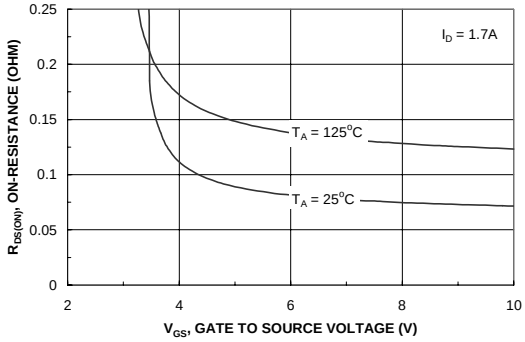


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

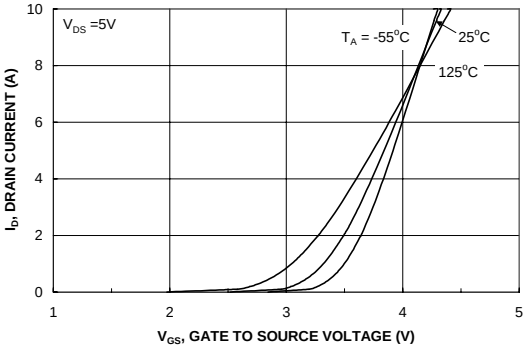


Figure 5. Transfer Characteristics.

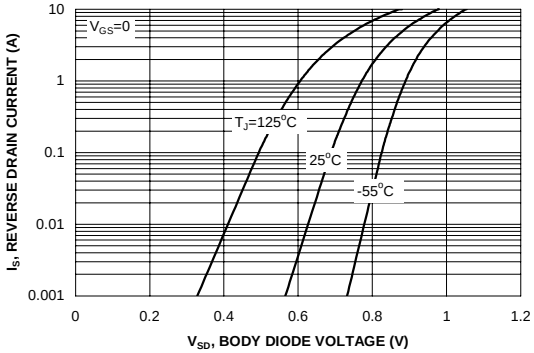
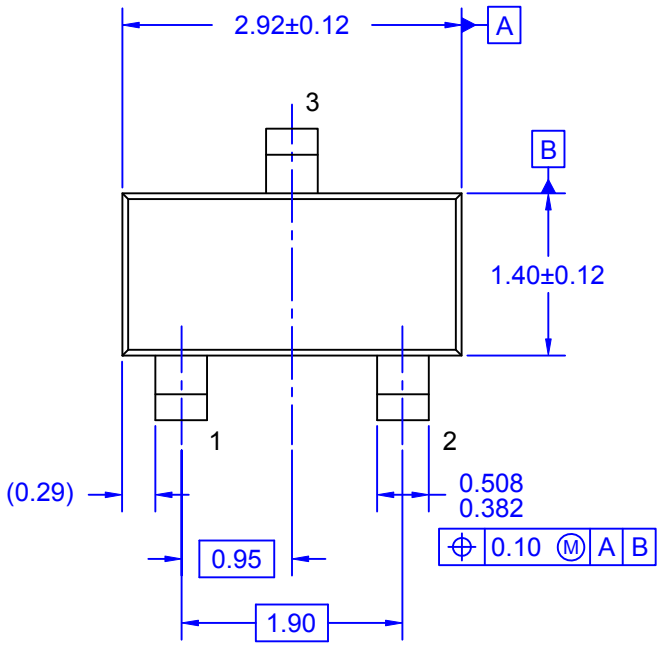
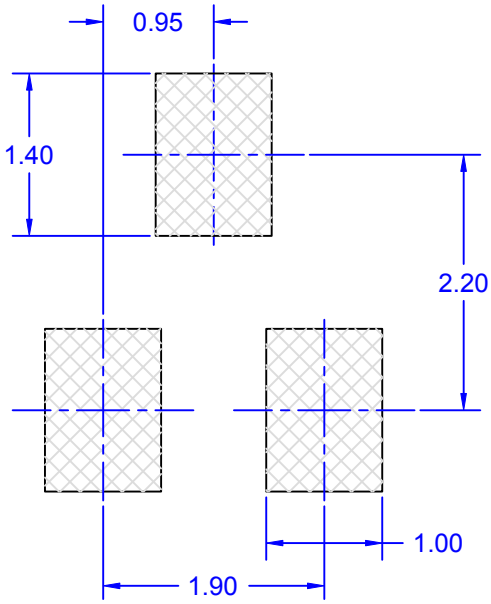
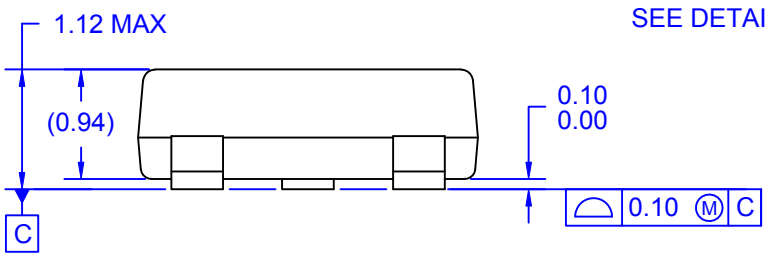


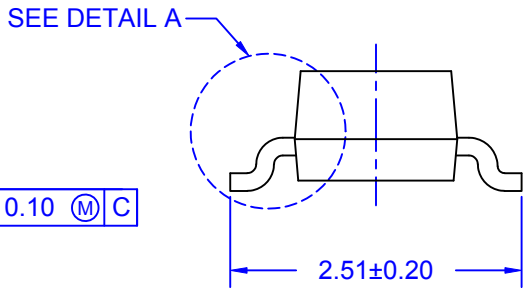
Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

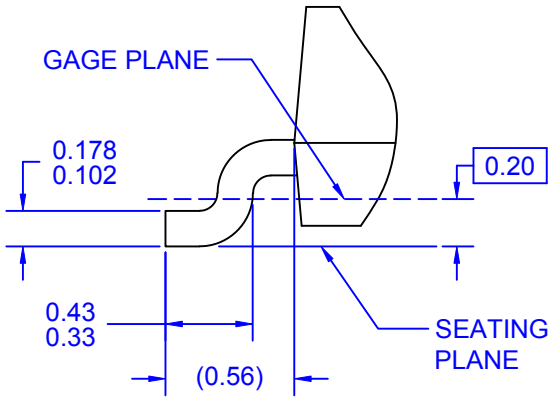




LAND PATTERN RECOMMENDATION







DETAIL A

SCALE: 50:1

NOTES: UNLESS OTHERWISE SPECIFIED

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Rev. I76